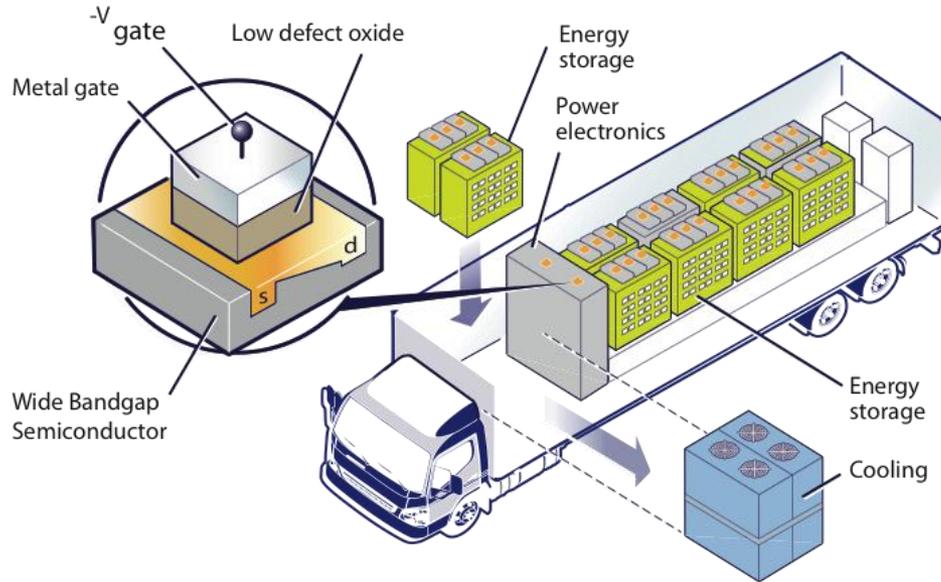


# Engineered Gate Oxides for Wide Bandgap Semiconductor MOSFETs

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## Purpose

- Gate dielectrics are a key limiter in GaN- and SiC-based power electronics technology
- Engineered gates will enable the development of robust MOSFETs

## Impact

- Reduced Cost
- Reduced Size
- Increased Performance and Reliability